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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No.

: 10/552,877

Applicant (s)

Kenneth E. Foster et al.

Filed

October 12, 2005

TC/A.U.

Unknown

Examiner

Unknown

Title

METHOD OF FILLING HIGH ASPECT RATIO, SMALL

DIMENSION GAPS AND FORMULATIONS USEFUL

THEREIN

Docket No.

62740A

Customer No.

00109

DEPOSITED WITH THE UNITED STATES POSTAL SERVICE AS FIRST CLASS MAIL WITH SUFFICIENT POSTAGE IN AN ENVELOPE ADDRESSED TO: ASSISTANT COMMISSIONER FOR PATENTS, WASHINGTON, DC 20231, ON:

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DATE OF SIGNATURE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

Pursuant to Applicant's duty of disclosure under 37 CFR §1.56, the Examiner's attention is directed to the information identified in the attached Form PTO/SB/08a.

The cited U.S. patents and patent application publications are listed on Form PTO/SB/08a. A copy of the cited foreign patent documents and non-patent literature are enclosed herewith. The Examiner is requested to review each reference and formulate his/her own understanding htereof.

This Statement is being submitted before the mailing date of the first Office Action on the merits. Under 37 C.F.R. §1.97(b)(3), submission of this Statement requires no fee. If this is incorrect, please charge any fees required to Deposit Account No. 04-1512.

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SMZ/jmd

Respectfully submitted,

Susan Moeller Zerull Registration No. 38,367

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PTO/SB/08A (08-03) Approved for use through 7/31/2006. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 1 of 2

Complete if Known			
Application Number	10/552877		
Filing Date	April 15, 2004		
First Named Inventor	Kenneth E. Foster		
Art Unit	Not Assigned		
Examiner Name	Not Assigned		
Attorney Docket Number .	62740A		

Examiner Initials*	Cite No.1	Document Number	Publication Date (MM-DD-YYYY)	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	No. ' Number-Kind Code ² (if known)	(accegos of Holorain Figures Appear	
		US-5,965,679	Oct. 12, 1999	Godschalx et al.	
	,	US-6,280,794	Aug. 28, 2001	Tu et al.	
		US-6,352,591	March 5, 2002	Yieh et al.	
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		US-6,646,081	Nov. 11, 2003	Godschalx et al.	
		US-5,446,204	Aug. 29, 1995	Bryant et al.	
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		US-6,559,215	May 6, 2003	Mills et al.	
		US-2004/0241338	Dec. 2, 2004	Foster et al.	
		US-			
		US-		1	
		US-			

Examiner	Date	
Signature	Considered	

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Sheet 2

Examiner

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(Use as many sheets as necessary)						
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Art Unit	Not Assigned		
Examiner Name	Not Assigned		
Attorney Docket Number	62740A		

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	т6
		Mouloud Bakli et al., "Materials and Processing for 0.25 micron Multilevel Interconnect," Microelectronic Engineering 33, (1997) 175-188.	Ø
		W.C. Gau et al., "Copper Electroplating for future ultralarge scale integration interconnection,' J. Vac. Sci. Technology. A 18(2), 2000.	Ø
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		Juseon Goo et al., "A highly Manufacturable, Low-Thermal Budget, Void and Seam Free Pre-Metal Dielectric Process Using new SOG for beyond 60nm DRAM and other devices," Interational Electronic Device Manufactures (IEDM), Session 12 paper 03, 2001.	
		Jin-Hwa Heo et al., "Void Free and Low Stress Shallow Trench Isolation Technology using P-SOG for sub 0.1 micron Device," Symposium on VLSI section 14.1, 2002.	X
		S. J. Martin, et. al., Adv. Mater. 2000, I2, page 1769 & 1776, No. 23, December 1 (2000)	Ø
		Peter Van Zant, "Microchip Fabrication: A Practical Guide to Semiconductor Processing," 4th edition, McGraw-Hill, 2000, Chapter 1, page 14 and chapter 16, page 504-505.	
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		J.A. Mandelman, et al., "Challenges and Future Directions for the Scaling of Dynamic Random-access memory, IBM J. Res. & . Dev., Vol. 46, No. 2/3 March/May 2002.	Ø
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Examiner		Date				
Signature		Considered				
Examiner: Initial if reference considered, whether or not citation is in conformation with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next						

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